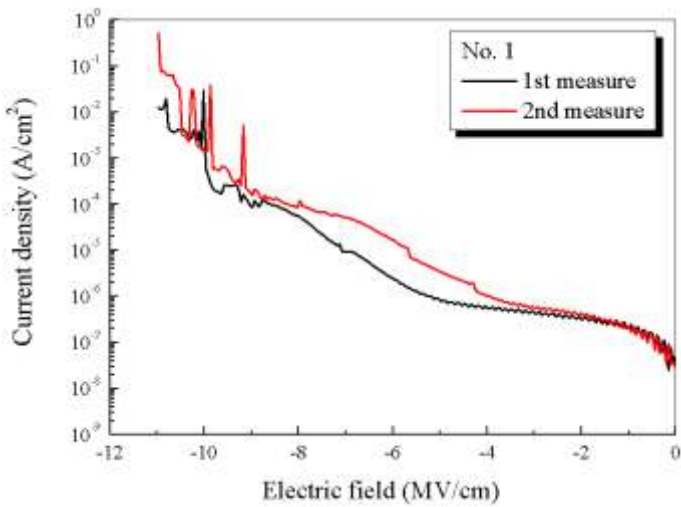
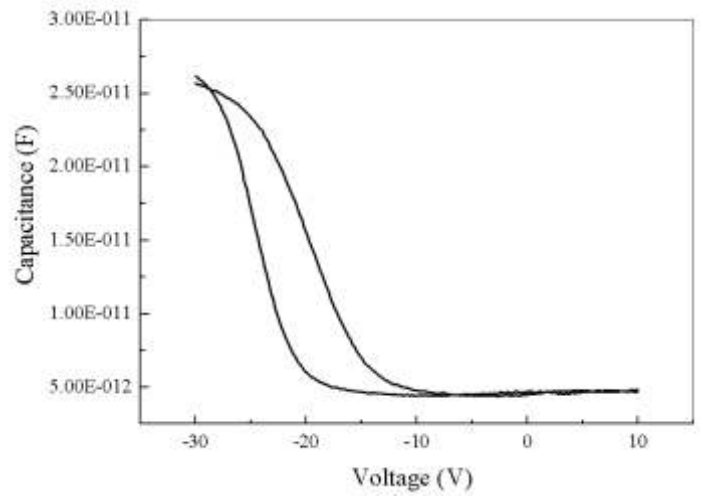


Plasmalab Data

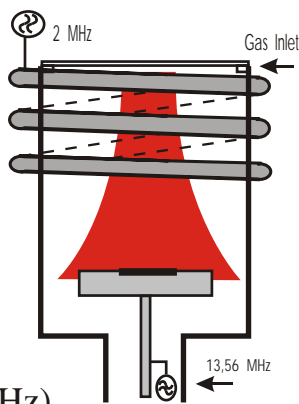
Low Temperature SiO₂ ICP - PECVD



Current density (A\ cm²) vs electrical field (MV\ cm)



Capacitance (F) vs Voltage (V)



Technology:

- PECVD
- with ICP Source (2 or 13 MHz)
- Inductive Coupled Plasma
- RF driven substrate electrode

Results:

- Rate: > 5 nm/ min
- temperature < 120 deg C
- lift off compatible
- refractive index 1.46
- breakdown voltage > 8 MV/ cm
- uniformity < +/- 4 % (100 mm wafer with ICP 380)

Plasmalab 80 Plus
Plasmalab System 100
Plasmalab System 133

